Solitron DEVICES, INC.

N-CHANNEL ENHANCEMENT MOS FET

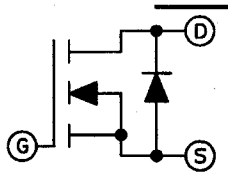
1000V, 9A, 1.4Ω

SDF9N100	JEA
SDF9N100	JEB
SDF9N100	JEC
SDF9N100	JED

FEATURES

- RUGGED PACKAGE
- HI-REL CONSTRUCTION
- CERAMIC EYELETS
- LEAD BENDING OPTIONS
- COPPER CORED 52 ALLOY PINS
- LOW IR LOSSES
- LOW THERMAL RESISTANCE
- OPTIONAL MIL-S-19500 SCREENING

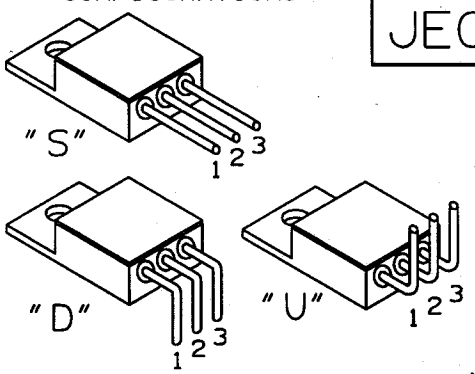
SCHEMATIC



TERMINAL CONNECTIONS			
G		H	
1	GATE	1	DRAIN
2	DRAIN	2	SOURCE
3	SOURCE	3	GATE

STANDARD BEND CONFIGURATIONS

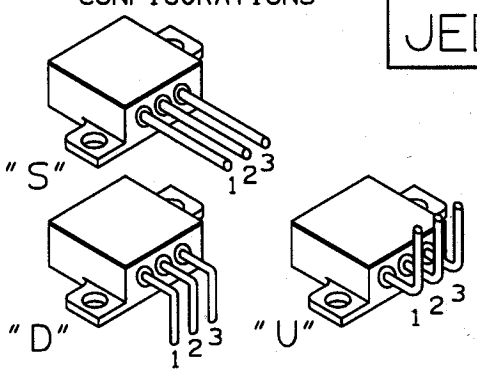
JEA
JEC



(CUSTOM BEND OPTIONS AVAILABLE)

STANDARD BEND CONFIGURATIONS

JEB
JED



(CUSTOM BEND OPTIONS AVAILABLE)

REL. 3/93

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL		UNITS
Drain-source Volt.(1)	VDSS	1000	Vdc
Drain-Gate Voltage (R_{GS}=1.0MΩ) (1)	VDGR	1000	Vdc
Gate-Source Voltage Continuous	VGS	±20	Vdc
Drain Current Continuous (Tc = 25°C)	ID	9	Adc
Drain Current Pulsed(3)	IDM	36	A
Total Power Dissipation	PD	300	W
Power Dissipation Derating > 25°C		2.4	W/°C
Operating & Storage Temp.	TJ/Tsig	-55 TO +150	°C
Thermal Resistance	RthJc	0.42	°C/W
Max.Lead temperature	TL	300	°C

ELECTRICAL CHARACTERISTICS T_C=25°C (UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-source Breakdown Volt.	V(BR)DSS	VGS=0V ID=250 µA	1000	-	-	V
Gate Threshold Voltage	VGS(TH)	VDS=VGS ID=250 µA	2.0	-	4.5	V
Gate Source Leakage	IGSS	VGS=±20 V	-	-	100	nA
Zero Gate Voltage Drain Current	IDSS	VDS=MAX.RATING VGS=0	-	-	250	µA
		VDS=0.8 MAX.RATING VGS=0 TJ=125°C	-	-	1000	µA
Static Drain-Source On-State Resistance(1)	RDS(ON)	VGS=10 V ID=4.5A	-	-	1.4	Ω
Forward Trans-Conductance (2)	gfs	VDS ≥ 50 V IDS=4.5A	6.0	-	-	S(℧)
Input Capacitance	CISS	VGS=0V VDS=25 V f=1.0 MHz	-	4500	-	pF
Output Capacitance	COSS		-	550	-	pF
Reverse Transfer Capacitance	CRSS		-	160	-	pF
Turn-On Delay	td(on)	VDD=500V Zo=50Ω ID=4.5A (MOSFET switching times are essentially independent of operating temp.)	-	-	100	ns
Rise Time	tr		-	-	110	ns
Turn-Off Delay	td(off)		-	-	220	ns
Fall Time	tf		-	-	105	ns
Total Gate Charge (Gate-Source Plus Gate-Drain)	Qg	VGS=10V, ID=9A VDS=0.8 MAX.RATING (Gate charge is essentially independent of the operating temperature)	-	145	-	nC
Gate-Source Charge	Qgs		-	55	-	nC
Gate-Drain ("Miller") Charge	Qgd		-	90	-	nC

SOURCE-DRAIN DIODE RATINGS & CHARACT. T_C=25°C (UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous Source Current (Body Diode)	IS	Modified MOSFET symbol showing the integral reverse P-N junction rectifier (See schematic)	-	-	9	A
Pulse Source Current (Body Diode) (1)	ISM		-	-	36	A
Diode Forward Voltage (2)	VSD	IF=9A VGS=0V Tc=+25°C	-	-	1.5	V
Reverse Recovery Time	trr	Tc=+25° C IF=9A di/dt=100A/µS	-	600	-	ns
Reverse Recovery Charge	Qrr		-	8.5	-	µC

(1) TJ = 25°C to 150°C.
(2) Pulse test: Pulse Width < 300µS, Duty Cycle < 2%.
(3) Repetitive Rating: Pulse Width limited By Max.junction Temperature.